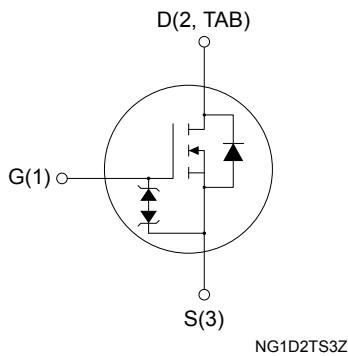
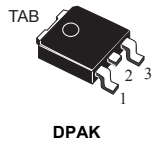


# N-channel 600 V, 370 mΩ typ., 10 A MDmesh DM2 Power MOSFET in a DPAK package



Order code	$V_{DS} @ T_{Jmax}$	$R_{DS(on)max.}$	$I_D$	$P_{TOT}$
STD11N60DM2	650 V	420 mΩ	10 A	110 W

- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

## Applications

- Switching applications

## Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM2 fast-recovery diode series. It offers very low recovery charge ( $Q_{rr}$ ) and time ( $t_{rr}$ ) combined with low  $R_{DS(on)}$ , rendering it suitable for the most demanding high-efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.



### Product status

STD11N60DM2

### Product summary

Order code	STD11N60DM2
Marking	11N60DM2
Package	DPAK
Packing	Tape and reel

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_{case} = 25\text{ }^\circ\text{C}$	10	A
	Drain current (continuous) at $T_{case} = 100\text{ }^\circ\text{C}$	6.3	
$I_{DM}^{(1)}$	Drain current (pulsed)	40	A
$P_{TOT}$	Total power dissipation at $T_{case} = 25\text{ }^\circ\text{C}$	110	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	50	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	
$T_{stg}$	Storage temperature range	-55 to 150	$^\circ\text{C}$
$T_j$	Operating junction temperature range		

1. Pulse width is limited by safe operating area.
2.  $I_{SD} \leq 10\text{ A}$ ,  $di/dt=900\text{ A}/\mu\text{s}$ ;  $V_{DS\text{ peak}} < V_{(BR)DSS}$ ;  $V_{DD} = 400\text{ V}$
3.  $V_{DS} \leq 480\text{ V}$ .

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.14	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50	

1. When mounted on 1 inch<sup>2</sup> FR-4 board, 2oz Cu.

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not repetitive	2.5	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	250	mJ

1. pulse width limited by  $T_{jmax}$
2. starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = I_{AR}$ ,  $V_{DD} = 50\text{ V}$ .

## 2 Electrical characteristics

( $T_{\text{case}} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$ , $I_{\text{D}} = 1\text{ mA}$	600			V
$I_{\text{DSS}}$	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$ , $V_{\text{DS}} = 600\text{ V}$			1.5	$\mu\text{A}$
		$V_{\text{GS}} = 0\text{ V}$ , $V_{\text{DS}} = 600\text{ V}$ , $T_{\text{case}} = 125\text{ }^{\circ}\text{C}^{(1)}$			100	
$I_{\text{GSS}}$	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$ , $V_{\text{GS}} = \pm 25\text{ V}$			$\pm 5$	$\mu\text{A}$
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$ , $I_{\text{D}} = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$ , $I_{\text{D}} = 5\text{ A}$		370	420	m $\Omega$

1. Defined by design, not subject to production test.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{\text{iss}}$	Input capacitance	$V_{\text{DS}} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{\text{GS}} = 0\text{ V}$	-	614	-	$\mu\text{F}$
$C_{\text{oss}}$	Output capacitance		-	32	-	
$C_{\text{riss}}$	Reverse transfer capacitance		-	1.08	-	
$C_{\text{oss eq.}}^{(1)}$	Equivalent output capacitance	$V_{\text{DS}} = 0\text{ to }480\text{ V}$ , $V_{\text{GS}} = 0\text{ V}$	-	57	-	$\mu\text{F}$
$R_{\text{G}}$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_{\text{D}} = 0\text{ A}$	-	6.2	-	$\Omega$
$Q_{\text{g}}$	Total gate charge	$V_{\text{DD}} = 480\text{ V}$ , $I_{\text{D}} = 10\text{ A}$ , $V_{\text{GS}} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	16.5	-	nC
$Q_{\text{gs}}$	Gate-source charge		-	3.8	-	
$Q_{\text{gd}}$	Gate-drain charge		-	9.2	-	

1.  $C_{\text{oss eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{\text{oss}}$  when  $V_{\text{DS}}$  increases from 0 to 80%  $V_{\text{DSS}}$ .

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d(on)}}$	Turn-on delay time	$V_{\text{DD}} = 300\text{ V}$ , $I_{\text{D}} = 5\text{ A}$ , $R_{\text{G}} = 4.7\text{ }\Omega$ , $V_{\text{GS}} = 10\text{ V}$ (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	11.7	-	ns
$t_{\text{r}}$	Rise time		-	6.3	-	
$t_{\text{d(off)}}$	Turn-off delay time		-	31	-	
$t_{\text{f}}$	Fall time		-	9.5	-	

**Table 7. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		10	A
$I_{SDM}^{(2)}$	Source-drain current (pulsed)		-		40	A
$V_{SD}^{(3)}$	Forward on voltage	$V_{GS} = 0\text{ V}$ , $I_{SD} = 10\text{ A}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 10\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	90		ns
$Q_{rr}$	Reverse recovery charge		-	248		nC
$I_{RRM}$	Reverse recovery current		-	5.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 10\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times )	-	160		ns
$Q_{rr}$	Reverse recovery charge		-	664		nC
$I_{RRM}$	Reverse recovery current		-	8.3		A

1. Limited by maximum junction temperature.
2. Pulse width is limited by safe operating area.
3. Pulse test: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

**Table 8. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 250\text{ }\mu\text{A}$ , $I_D = 0\text{ A}$	$\pm 30$	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

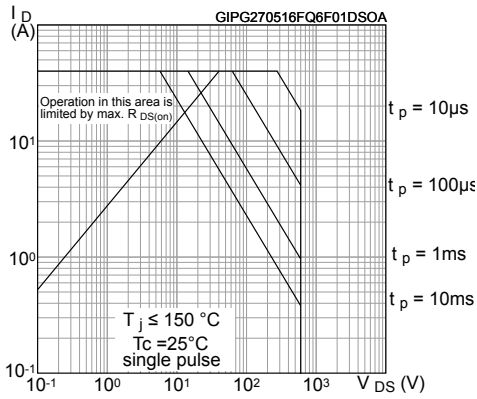


Figure 2. Thermal impedance

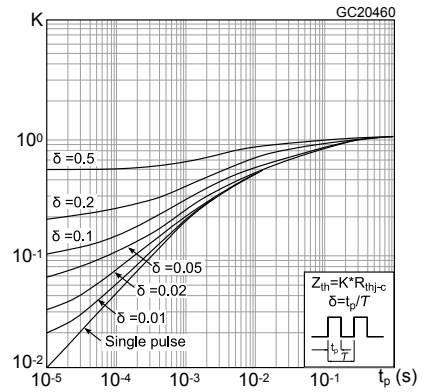


Figure 3. Output characteristics

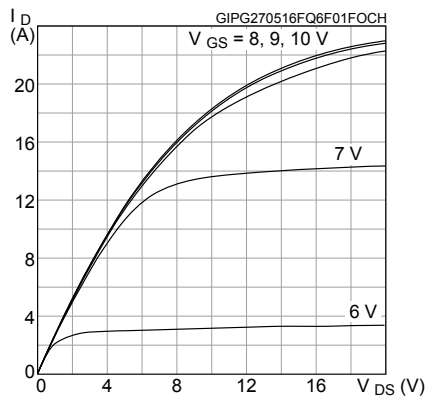


Figure 4. Transfer characteristics

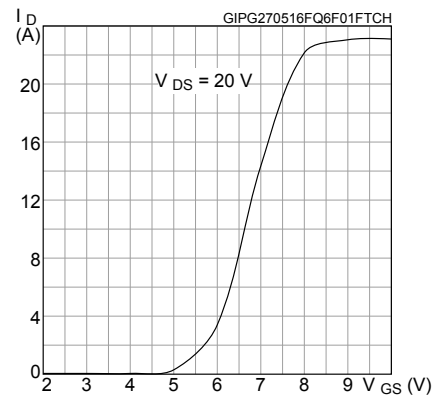


Figure 5. Gate charge vs gate-source voltage

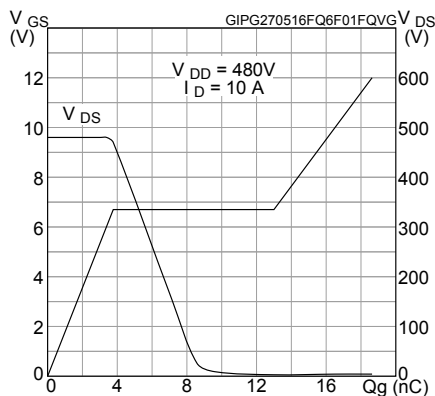


Figure 6. Static drain-source on-resistance

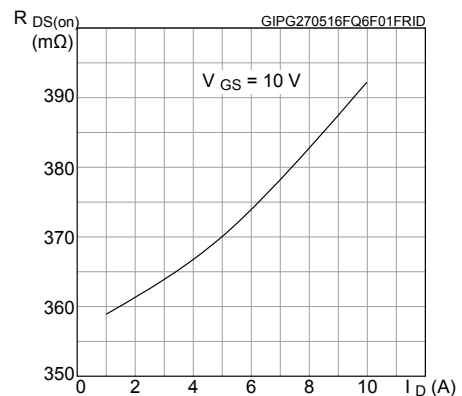


Figure 7. Capacitance variations

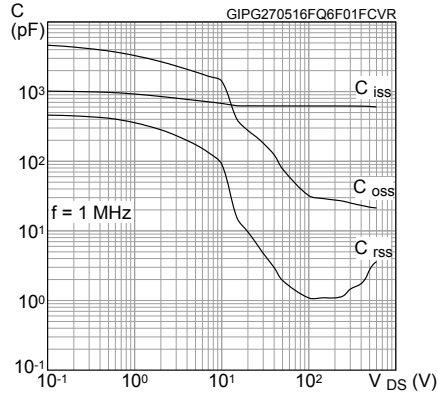


Figure 8. Normalized gate threshold voltage vs temperature

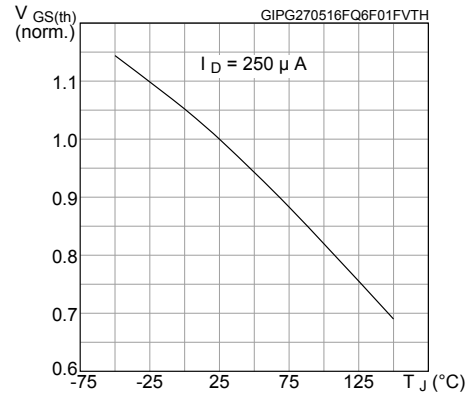


Figure 9. Normalized on-resistance vs temperature

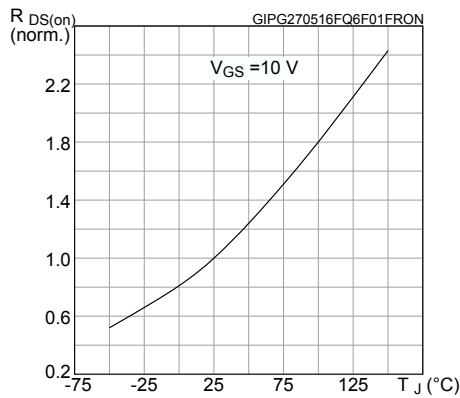


Figure 10. Normalized V<sub>(BR)DSS</sub> vs temperature

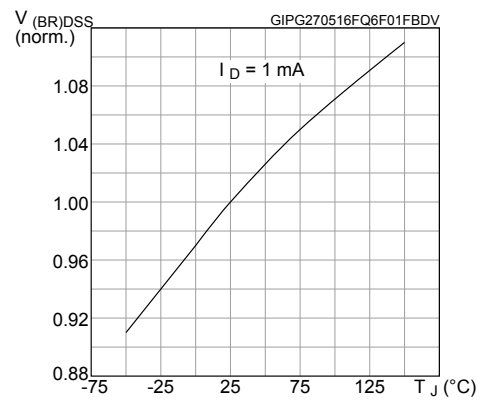


Figure 11. Output capacitance stored energy

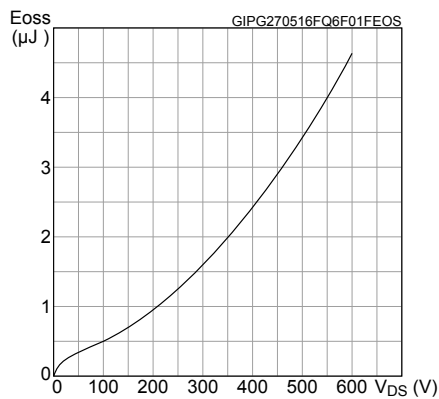
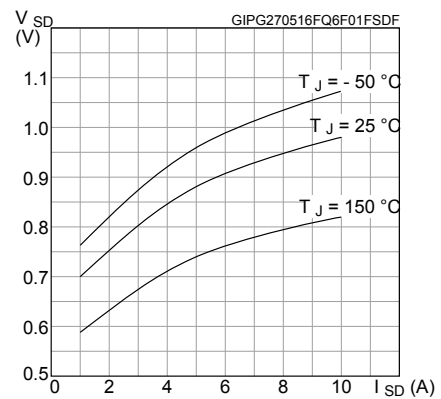


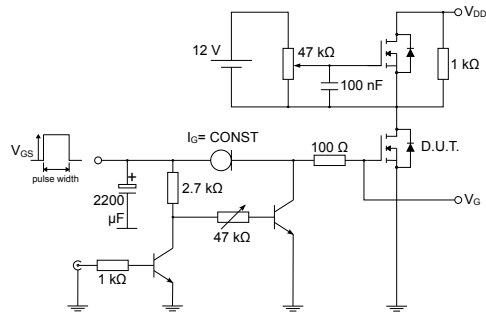
Figure 12. Source-drain diode forward characteristics



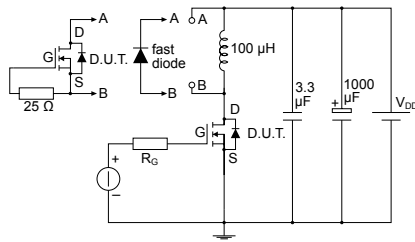
### 3 Test circuits

**Figure 13. Test circuit for resistive load switching times**


AM01468v1

**Figure 14. Test circuit for gate charge behavior**


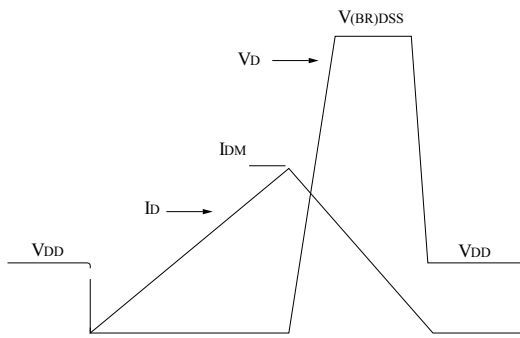
AM01469v1

**Figure 15. Test circuit for inductive load switching and diode recovery times**


AM01470v1

**Figure 16. Unclamped inductive load test circuit**


AM01471v1

**Figure 17. Unclamped inductive waveform**


AM01472v1

**Figure 18. Switching time waveform**


AM01473v1

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## 4 Package information

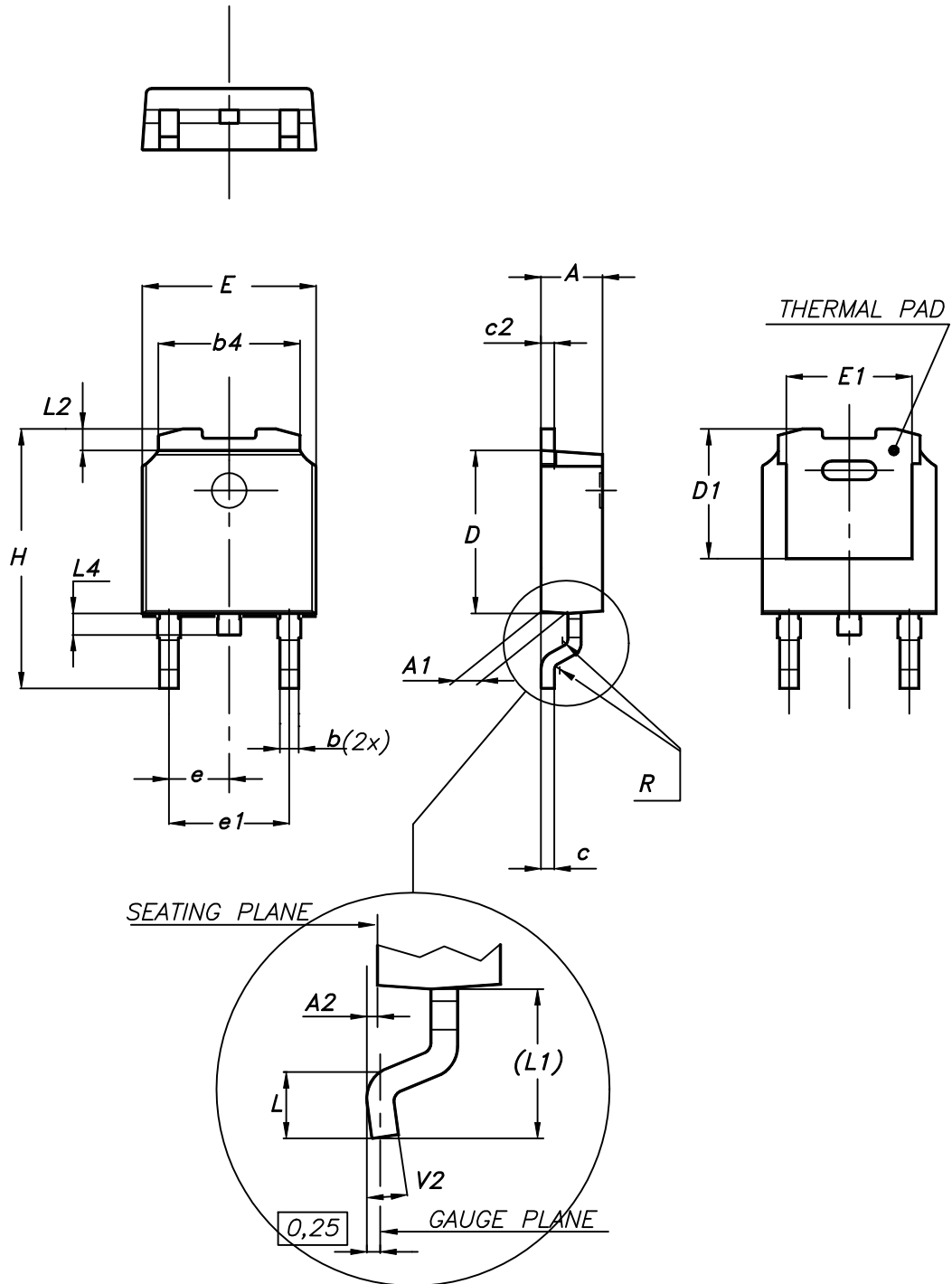
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In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.



### 4.1 DPAK (TO-252) type A2 package information

Figure 19. DPAK (TO-252) type A2 package outline

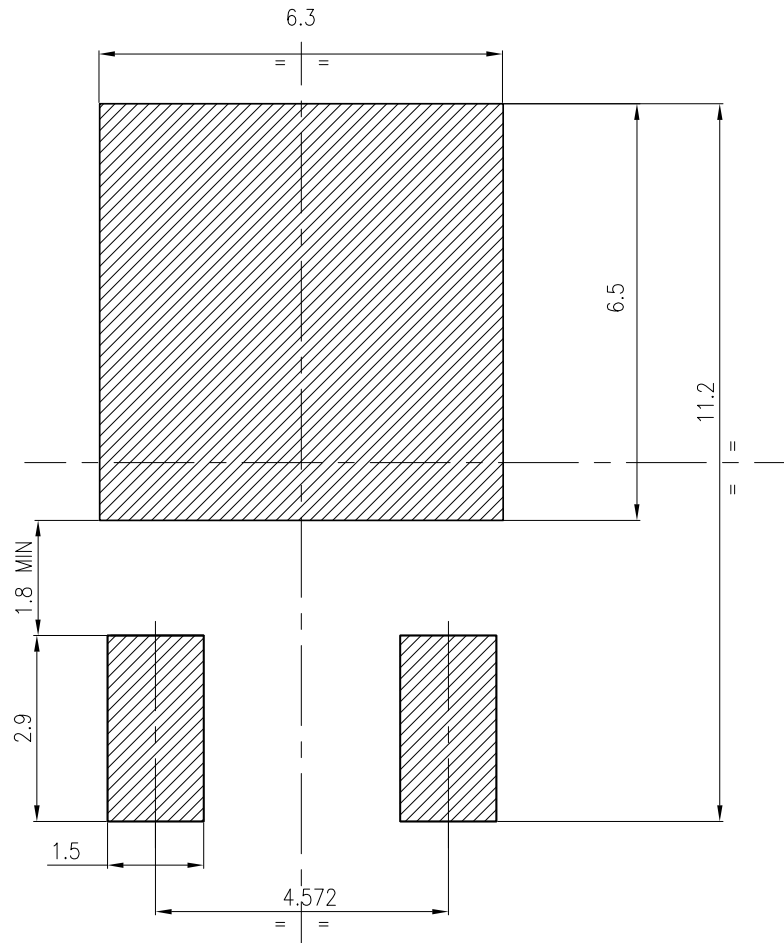


0068772\_type-A2\_rev26

**Table 9. DPAK (TO-252) type A2 mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

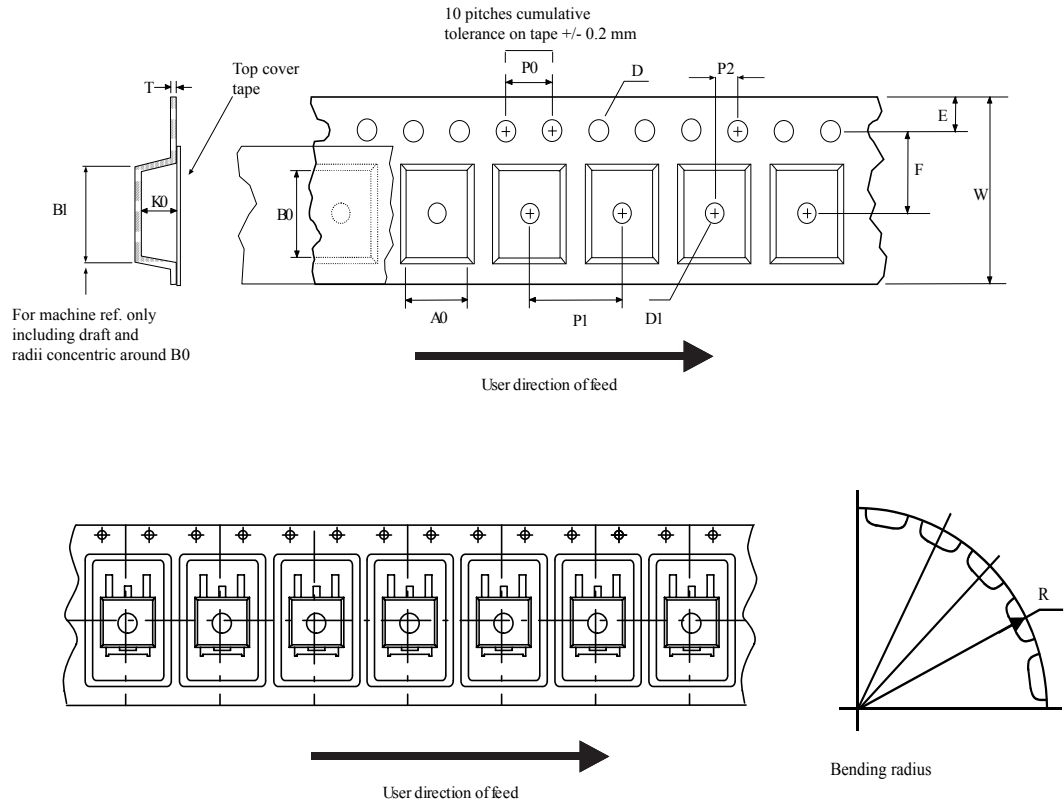
Figure 20. DPAK (TO-252) recommended footprint (dimensions are in mm)



FP\_0068772\_26

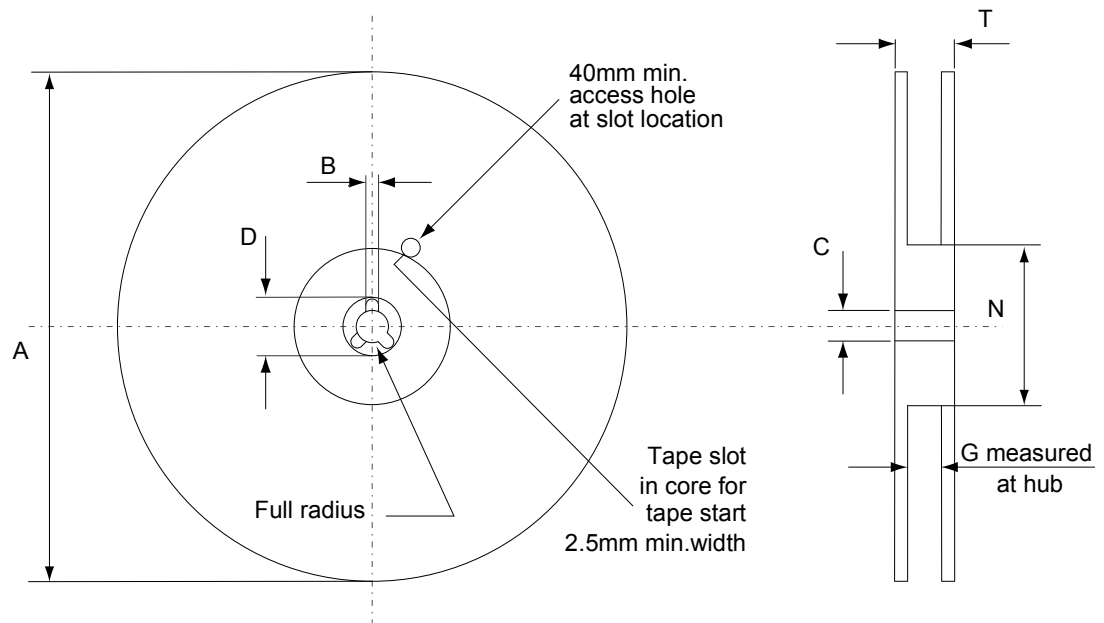
## 4.2 DPAK (TO-252) packing information

Figure 21. DPAK (TO-252) tape outline



AM08852v1

Figure 22. DPAK (TO-252) reel outline



AM06038v1

Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

## Revision history

**Table 11. Document revision history**

Date	Revision	Changes
17-Jun-2016	1	First release.
04-Nov-2019	2	Modified <a href="#">Table 1. Absolute maximum ratings</a> and <a href="#">Table 4. Static</a> . Updated <a href="#">Section 4.1 DPAK (TO-252) type A2 package information</a> . Minor text changes.

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